

**AMENDMENT TO THE SPECIFICATION:**

Please replace the paragraph beginning on page 2, line 24, of the specification with the following rewritten paragraph.

While in simple plasma patterning processes, an increase in the plasma power, because of the resulting increased production of ions and etching species, gives rise to the desired increase in the etching rate, in the case of the method according to German Patent 42 41 045 C1, the deposition steps must also be taken into account in addition to the etching steps. In this context, an increase in the plasma power during the etching steps not only results in the desired increased production of etching species and ions but also changes the deposition steps in a characteristic manner.